



Bipolar PNP Bare Die – BTP6099

Part Description

The BTP6099 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6099

Key Parameters:

- VCBO = -100V
- VCEO = -60V
- VEBO = -6V
- hFE = 120-300 @ VCE = -1V, IC = -2A
- VCE(Sat) = -0.46V @ IC = -5A, IB = -500mA
- fT = 130 MHz @ VCE = -10V, IE = 0A
- COBO = 72pF @ VCB = -10V

Features

Low VCE(sat). Designed to provide performance equivalent to ZETEX / DIODES INC. FZT591

Die Size (Unawn)

1670 μ m X 1670 μ m, 66 Mils X 66 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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